TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

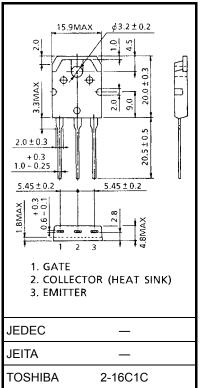
GT10Q101

High Power Switching Applications

- Third-generation IGBT
- Enhancement mode type
- High speed: $t_f = 0.32 \ \mu s \ (max)$
- Low saturation voltage: VCE (sat) = 2.7 V (max)

Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit	
Collector-emitter voltage		V _{CES}	1200	V	
Gate-emitter voltage		V _{GES}	±20	V	
Collector current	DC	Ι _C	10	A	
	1 ms	I _{CP}	20		
Collector power dissipation		Pc	140	W	
(Tc = 25°C)		ГC	140		
Junction temperature		Тј	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	



Weight: 4.6 g (typ.)

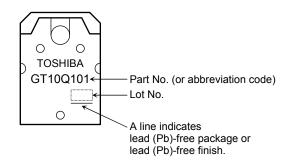
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the

reliability significantly even if the operating conditions (i.e.

operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Marking

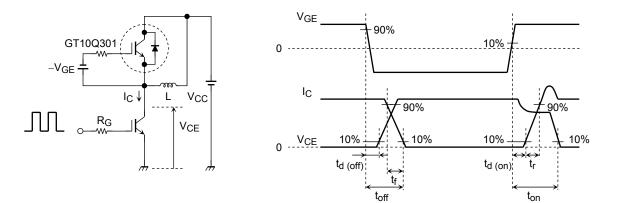


Unit: mm

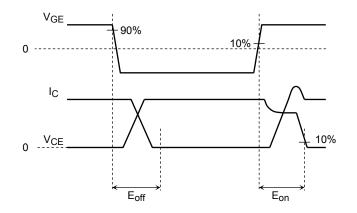
Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GES}	$V_{GE}=\pm 20~V,~V_{CE}=0$	_		±500	nA
Collector cut-off current		ICES	$V_{CE} = 1200 V, V_{GE} = 0$	_	_	1.0	mA
Gate-emitter cut-off voltage		V _{GE (OFF)}	$I_C = 1 \text{ mA}, V_{CE} = 5 \text{ V}$	4.0	_	7.0	V
Collector-emitter saturation voltage		V _{CE (sat)}	$I_{C} = 10 \text{ A}, V_{GE} = 15 \text{ V}$	_	2.1	2.7	V
Input capacitance		Cies	$V_{CE}=50~V,~V_{GE}=0,~f=1~MHz$		600	_	pF
Switching time	Rise time	tr	Inductive Load $V_{CC}=600 \text{ V}, \text{ I}_{C}=10 \text{ A}$ $V_{GG}=\pm15 \text{ V}, \text{ R}_{G}=75 \Omega \tag{Note1}$		0.07	_	μs
	Turn-on time	t _{on}			0.30		
	Fall time	t _f			0.16	0.32	
	Turn-off time	t _{off}			0.50		
Thermal resistance		R _{th (j-c)}	_	_		0.89	°C/W

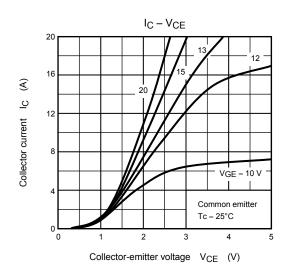
Note1: Switching time measurement circuit and input/output waveforms

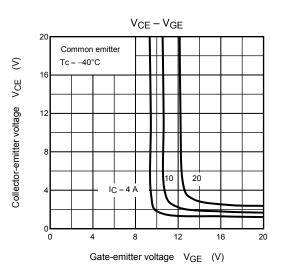


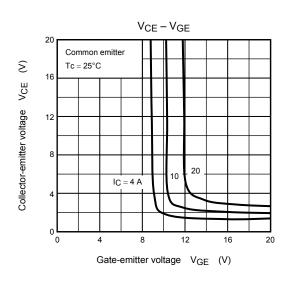
Note2: Switching loss measurement waveforms

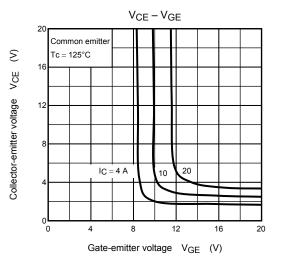


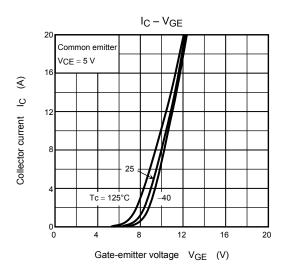
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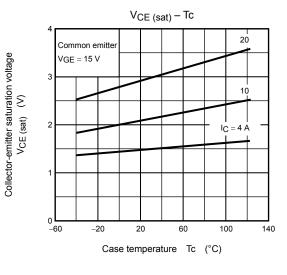




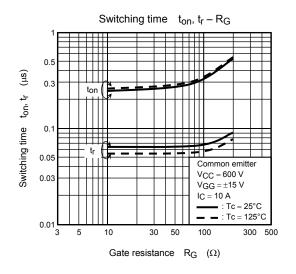


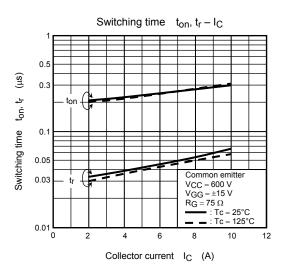




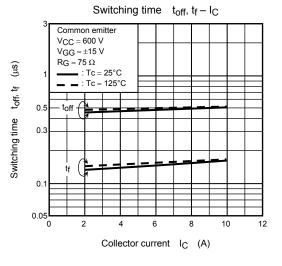


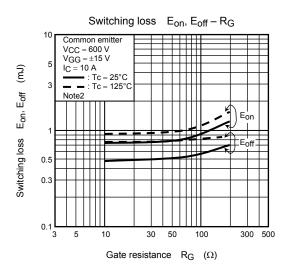
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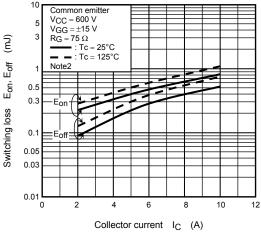


Switching time $t_{off}, t_f - R_G$ Common emitter VCC = 600 V $V_{GG} = \pm 15 V$ $I_C = 10 A$ (sıı) : Tc = 25°C t_{off}, tf __ : Tc = 125°C Switching time 0.5 toff 0.3 tf 0.1 0.05 30 300 500 3 5 10 50 100 Gate resistance R_G (Ω)



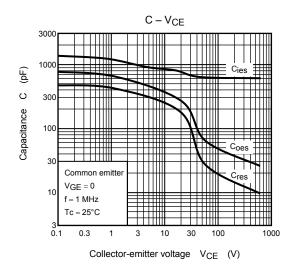


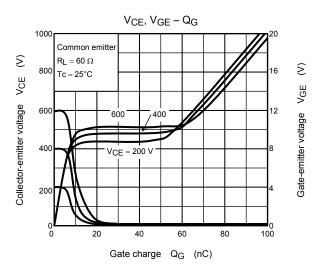
Switching loss Eon, Eoff - IC



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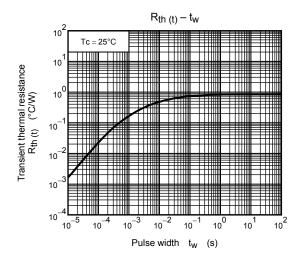
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Safe operating area 100 50 IC max (pulsed) 30 Ш € IC max (continuous) 100 50 μs 10 <u>ں</u> DC Collector current -5 3 operation : Single nonrepetitive pulse Tc = 25°C 0.5 . Curves must be derated linearly with 0.3 increase in temperature 0.1 3 10 30 100 300 1000 3000 Collector-emitter voltage V_{CE} (V)

Reverse bias SOA 50 30 € 10 <u>ں</u> Collector current 0.5 Tj≦ 125°C 0.3 VGE = ±15 V $RG = 75 \Omega$ 0.1 3 10 3000 30 300 1000 1 100 Collector-emitter voltage V_{CE} (V)



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20070701-EN

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